

ZXTP19020DG 20V PNP high gain transistor in SOT223

Summary

 $BV_{CEO} > -20V$

 $BV_{ECO} > -4V$

 $I_{C(cont)} = 8A$

 $V_{CE(sat)} < -47 \text{mV} @ -1A$

 $R_{CE(sat)} = 28m\Omega$

 $P_{D} = 3.0W$

Complementary part number ZXTN19020DG

B

Description

Packaged in the SOT223 outline this new low saturation PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions.

Features

- · Higher power dissipation SOT223 package
- · High gain
- · High peak current
- · Low saturation voltages
- 4V reverse blocking voltage

Applications

- · Power disconnect switch
- · High side drivers
- Motor drive

C ______ C _______ B

Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP19020DGTA	7	12	1000

Device marking

ZXTP19020D

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-Base voltage	V _{CBO}	-25	V
Collector-Emitter voltage	V _{CEO}	-20	V
Emitter-Collector voltage (reverse blocking)	V _{ECO}	-4	V
Emitter-Base voltage	V _{EBO}	-7	V
Continuous Collector current ^(c)	I _C	-8	Α
Base current	I _B	-1	Α
Peak pulse current	I _{CM}	-15	Α
Power dissipation at T _A =25°C ^(a)	P _D	1.2	W
Linear derating factor		9.6	mW/°C
Power dissipation at T _A =25°C ^(b)	P _D	1.6	W
Linear derating factor		12.8	mW/°C
Power dissipation at T _A =25°C ^(c)	P _D	3.0	W
Linear derating factor		24	mW/°C
Power dissipation at T _A =25°C ^(d)	P _D	5.3	W
Linear derating factor		42	mW/°C
Power dissipation at T _C =25°C ^(e)	P _D	10.2	W
Linear derating factor		81	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to 150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit	
Junction to ambient ^(a)	$R_{\Theta JA}$	104	°C/W	
Junction to ambient ^(b)	$R_{\Theta JA}$	78	°C/W	
Junction to ambient ^(c)	$R_{\Theta JA}$	42	°C/W	
Junction to ambient ^(d)	$R_{\Theta JA}$	23.5	°C/W	
Junction to case ^(e)	$R_{\Theta JC}$	12.3	°C/W	

NOTES:

⁽a) For a device surface mounted on 15mm x 15mm x 0.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

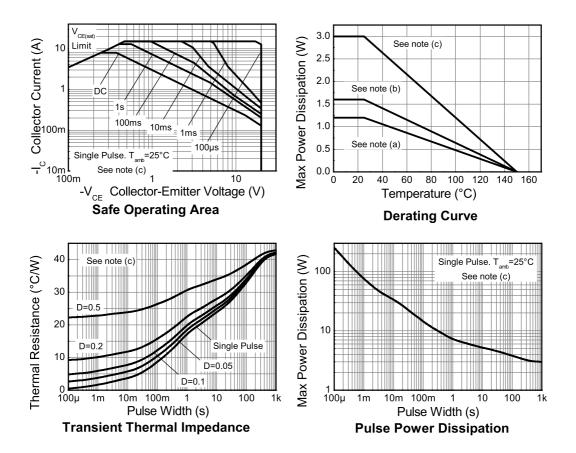
 $[\]textbf{(b)}\,Mounted\,\,on\,\,25mm\,\,x\,\,25mm\,\,x\,\,0.6mm\,\,FR4\,\,PCB\,\,with\,\,high\,\,coverage\,\,of\,\,single\,\,sided\,\,1oz\,\,copper,\,\,in\,\,still\,\,air\,\,conditions.$

⁽c) Mounted on $50 \text{mm} \times 50 \text{mm} \times 0.6 \text{mm}$ FR4 PCB with high coverage of single sided 2 oz copper, in still air conditions.

⁽d) As (c) above measured at t<5 seconds.

⁽e) Junction to case (collector tab). Typical

Thermal characteristics



Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

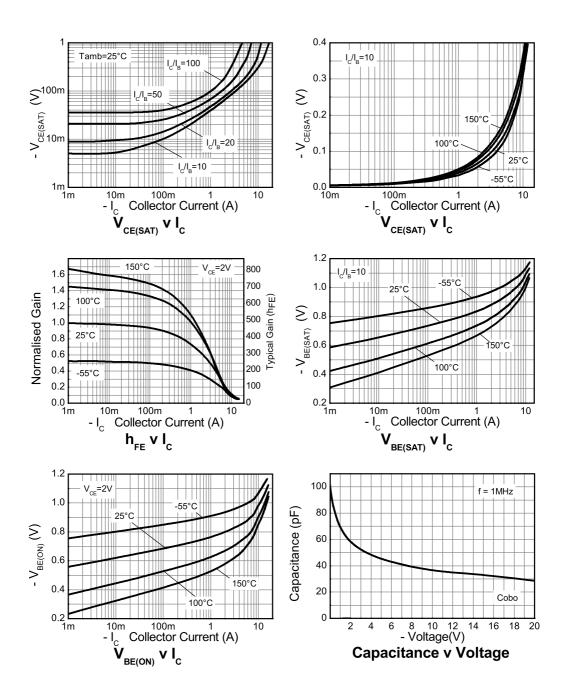
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-Base breakdown voltage	BV _{CBO}	-25	-55		V	$I_C = -100\mu A$
Collector-Emitter breakdown voltage	BV _{CEO}	-20	-50		V	I _C = -10mA ^(*)
Emitter-Collector breakdown voltage (reverse blocking)	BV _{ECX}	-4	-8.6		V	I_E = -100μA, R_{BC} < 1kΩ or 0.25V > V_{BC} > -0.25V
Emitter-Collector breakdown voltage (reverse blocking)	BV _{ECO}	-4	-8.6		V	$I_E = -100 \mu A$
Emitter-Base breakdown voltage	BV _{EBO}	-7	-8.2		V	I _E = -100μA
Collector-Base cut-off	I _{CBO}		<1	50	nA	$V_{CB} = -25V$
current				0.5	μΑ	$V_{CB} = -25V, T_{amb} = 100^{\circ}C$
Emitter cut-off current	I _{EBO}		<1	-50	nA	$V_{EB} = -5.6V$
Collector-Emitter	V _{CE(sat)}		-40	-47	mV	$I_C = -1A$, $I_B = -100 \text{mA}^{(*)}$
saturation voltage			-97	-130	mV	$I_C = -1A$, $I_B = -10mA^{(*)}$
			-115	-145	mV	$I_C = -2A$, $I_B = -40mA^{(*)}$
			-220	-275	mV	$I_C = -8A$, $I_B = -800 \text{mA}^{(*)}$
Base-Emitter saturation voltage	V _{BE(sat)}		-1050	-1150	mV	$I_C = -8A$, $I_B = -800 \text{mA}^{(*)}$
Base-Emitter turn-on voltage	V _{BE(on)}		-930	-1000	mV	$I_C = -8A$, $V_{CE} = -2V^{(*)}$
Static forward current	h _{FE}	300	450	900		$I_C = -100 \text{mA}, V_{CE} = -2V^{(*)}$
transfer ratio		200	290			$I_C = -2A$, $V_{CE} = -2V^{(*)}$
		45	70			$I_C = -8A$, $V_{CE} = -2V^{(*)}$
			25			$I_C = -15A$, $V_{CE} = -2V^{(*)}$
Transition frequency	f _T		176		MHz	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V}$ f = 50MHz
Input capacitance	C _{ibo}			400	рF	$V_{EB} = -0.5V, f = 1MHz^{(*)}$
Output capacitance	C _{obo}		36	45	pF	V _{CB} = -10V, f = 1MHz ^(*)
Delay time	t _d		23		ns	
Rise time	t _r		18.4		ns	$I_C = -1A$, $V_{CC} = -10V$,
Storage time	t _s		266		ns	$I_{B1} = -I_{B2} = -50 \text{mA}$
Fall time	t _f		49.6		ns	

NOTES:

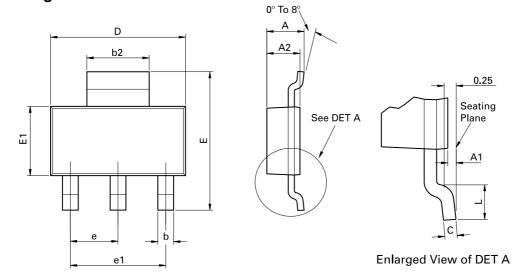
^(*) Measured under pulsed conditions. Pulse width \leq 300 μ s; duty cycle \leq 2%.



Typical characteristics



Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

Dim.	Millin	neters	Inc	hes	Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
Α	-	1.80	-	0.071	D	6.30	6.70	0.248	0.264
A1	0.02	0.10	0.0008	0.004	е	2.30	BSC	0.090	5 BSC
A2	1.55	1.65	0.0610	0.0649	e1	4.60	BSC	0.181	BSC
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
С	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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